# SDS160EWT

# SILICON EPITAXIAL PLANAR SWITCHING DIODE

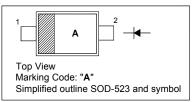
for ultra high speed switching application

#### **Features**

- Fast reverse recovery time
- · Small total capacitance
- · Low forward voltage

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ( $T_a = 25$  °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Forward Current	Io	100	mA
Peak Forward Current	I <sub>FM</sub>	300	mA
Surge Current (10 ms)	I <sub>FSM</sub>	2	Α
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>stg</sub>	- 55 to + 150	°C

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	1.2	V
Reverse Current at V <sub>R</sub> = 80 V	I <sub>R</sub>	0.5	μΑ
Total Capacitance at $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$	Ст	3	pF
Reverse Recovery Time at $I_{rr}$ = 0.1 X $I_{R}$ , $I_{F}$ = $I_{R}$ = 10 mA, $R_{L}$ = 100 $\Omega$	t <sub>rr</sub>	4	ns

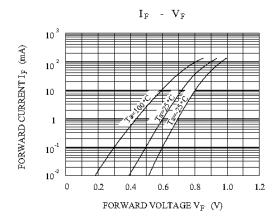


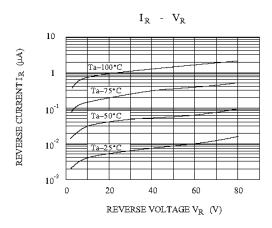


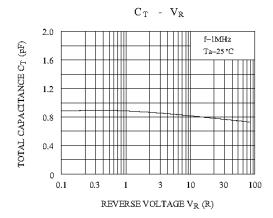


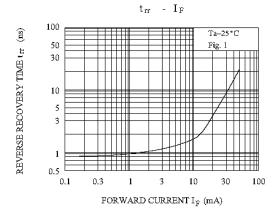






















### **PACKAGE OUTLINE**

### Plastic surface mounted package; 2 leads

**SOD-523** 

